

1N458 • 1N458A

LOW LEAKAGE

DIFFUSED SILICON PLANAR* DIODES

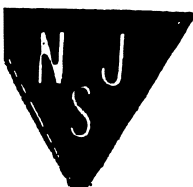
- BV . . . 150 V (MIN) @ 100 μ A
- I_R . . . 25 nA (MAX) @ 125 V 1N458

ABSOLUTE MAXIMUM RATINGS (Note 1)

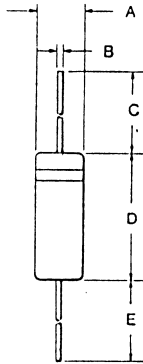
Maximum Temperatures		
Storage Temperature		-65°C to +200°C
Operating Temperature		175°C
Maximum Power Dissipation		
Total Dissipation at 25°C Ambient Temperature		400 mW
Maximum Voltage and Currents		
WIV Working Inverse Voltage		125 V
I _O Average Rectified Current		55 mA
I _F Forward Current Steady State DC		115 mA
I _f Recurrent Peak Forward Current		175 mA
i _f (surge) Peak Forward Surge Current		500 mA
	Pulse Width = 1.0 s	2.0 A
	Pulse Width = 1.0 μ s	

ELECTRICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted)

SYMBOL	CHARACTERISTIC	1N458		1N458A		UNITS	TEST CONDITIONS
		MIN.	MAX.	MIN.	MAX.		
V _F	Forward Voltage		1.0			V	I _F = 7.0 mA
I _R	Reverse Current		25		1.0	V	I _F = 100 mA
					5.0	nA	V _R = 125 V
			5.0	5.0		nA	V _R = 125 V
BV	Breakdown Voltage	150		150		V	V _R = 125 V, T _A = 150°C
C	Capacitance (Note 2)		6.0			pF	I _R = 100 μ A V _R = 0, f = 1.0 MHz



Glass Diode (DO-7) outline



NOTES: See table for dimensions in inches and millimeters
 .020 diameter dumet leads, tinned or gold-plated
 Hermetically sealed glass
 Package weight is 0.25 grams

DIM.	INCHES			MILLIMETERS		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			0.105			2.67
B		0.02			0.508	
C	1.0			25.40		
D			0.300			7.62
E	1.0			25.40		